POWERSEM

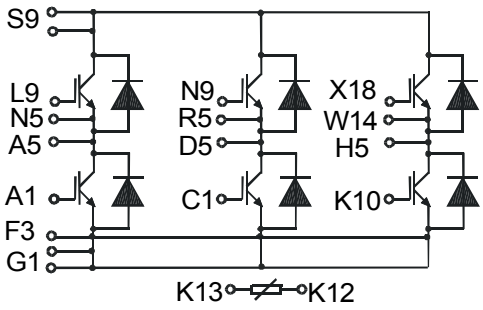
ECO-PAC™ 2

IGBT Module PSII 24/06*

Sixpack

Preliminary Data Sheet

I_{C25} = 19 A
V_{CES} = 600 V
$V_{CE(sat)typ.}$ = 1.9 V



PSII 24/06*

*NTC optional

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	600	V
V_{GES}		± 20	V
I_{C25}	T_C = 25°C	19	A
I_{C80}	T_C = 80°C	14	A
I_{CM}	V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C	20	A
V_{CEK}	RBSOA, Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = 720 V; V_{GE} = ±15 V; R_G = 82 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	73	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 10 A; V_{GE} = 15 V; T_{VJ} = 25°C		1.9	2.4	V
	T_{VJ} = 125°C		2.2		V
$V_{GE(th)}$	I_C = 0.35 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.6	mA
	T_{VJ} = 125°C		2.7		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			100	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		35		ns
t_r	V_{CE} = 300 V; I_C = 10 A		35		ns
$t_{d(off)}$	V_{GE} = ±15 V; R_G = 82 Ω		230		ns
t_f			30		ns
E_{on}			0.4		mJ
E_{off}			0.3		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		600		pF
Q_{Gon}	V_{CE} = 300 V; V_{GE} = 15 V; I_C = 10 A		39		nC
R_{thJC}	(per IGBT)			1.7	K/W
R_{thJH}	with heatsink compound (0.42 K/m.K; 50 µm)		3.4		K/W

Features

- NPT IGBT's
  - positive temperature coefficient of saturation voltage
  - fast switching
- FRED diodes
  - fast reverse recovery
  - low forward voltage
- Industry Standard Package
  - solderable pins for PCB mounting
  - isolated DCB ceramic base plate
- UL registered, E 148688

Applications

- AC drives
- power supplies with power factor correction

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

POWERSEM GmbH, Walpersdorfer Str. 53
D - 91126 Schwabach
Phone: 09122 - 9764 - 0 FAX: 09122 - 9764 - 20

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	21	A
I_{F80}	T_C = 80°C	14	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 10 A; T_{VJ} = 25°C		1.9	2.1	V
	T_{VJ} = 125°C		1.4		V
I_{RM}	I_F = 10 A; di_F/dt = -400 A/µs; T_{VJ} = 125°C		11		A
t_{rr}	V_R = 300 V; V_{GE} = 0 V		80		ns
R_{thJC}				3.5	K/W
R_{thJH}	with heatsink compound (0.42 K/m.K; 50 µm)		7.0		K/W

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

Temperature Sensor NTC

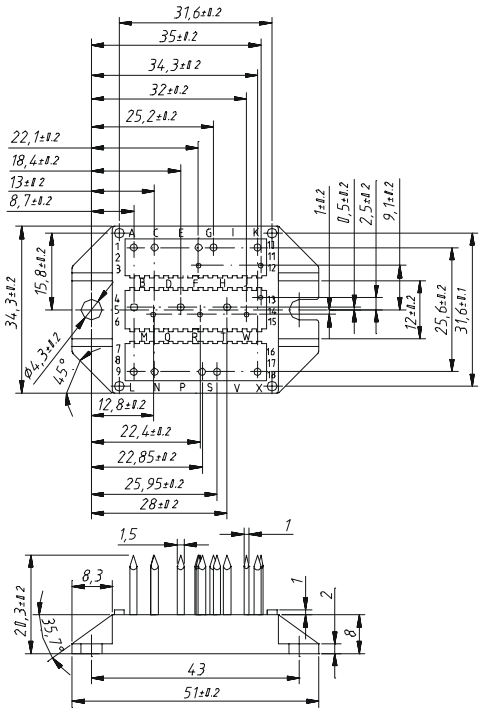
Symbol	Conditions	Characteristic Values min.	typ.	max.	
R_{25}	T = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$			3375		K

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	$I_{ISOL} \leq$ 1 mA; 50/60 Hz; t = 1 s	3600	V~
M_d	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values min.	typ.	max.	
d_S	Creepage distance on surface (Pin to heatsink)	11.2			mm
d_A	Strike distance in air (Pin to heatsink)	11.2			mm
Weight			24		g

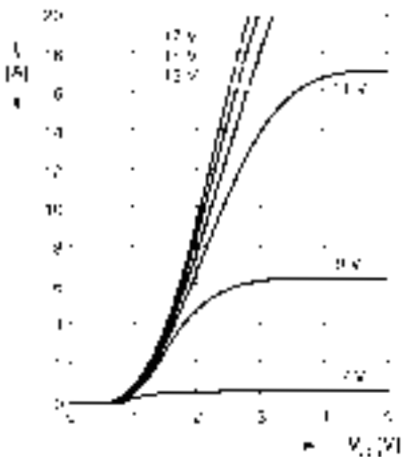
Package style and outline
Dimensions in mm (1mm = 0.0394“)



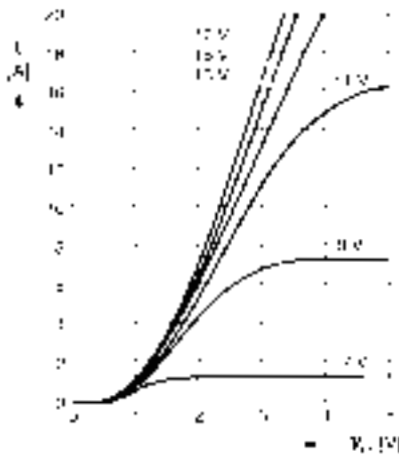
POWERSEM GmbH, Walpersdorfer Str. 53
D - 91126 Schwabach
Phone: 09122 - 9764 - 0 FAX: 09122 - 9764 - 20

IGBT

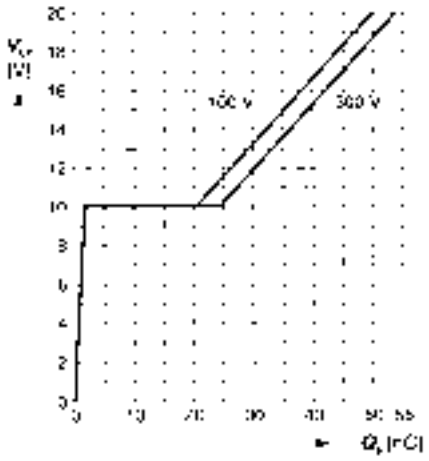
Typ. output characteristics



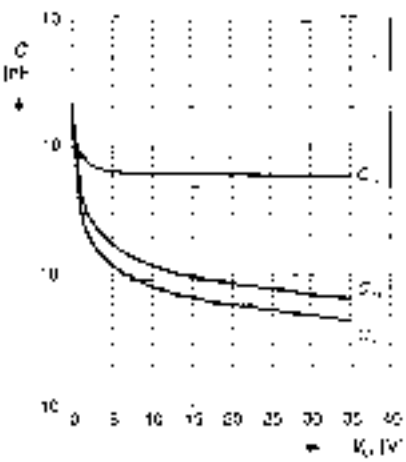
Typ. output characteristics



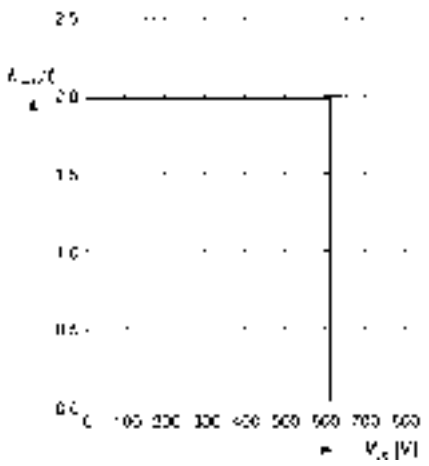
Typ. gate charge



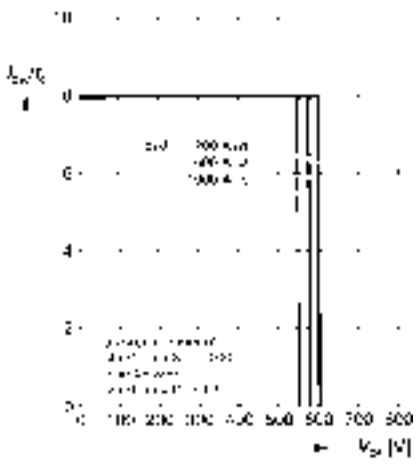
Typ. capacitances



Reverse biased safe operating area

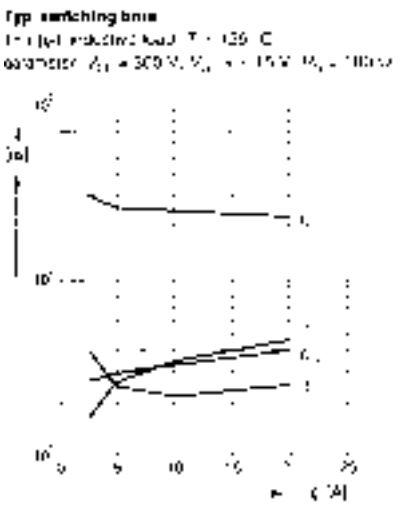


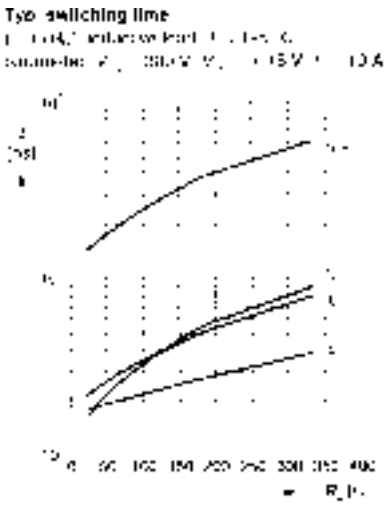
Short circuit safe operating area

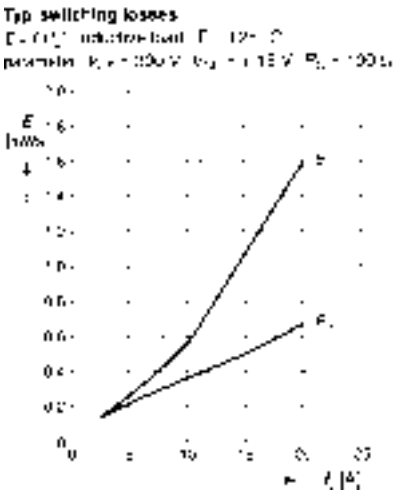


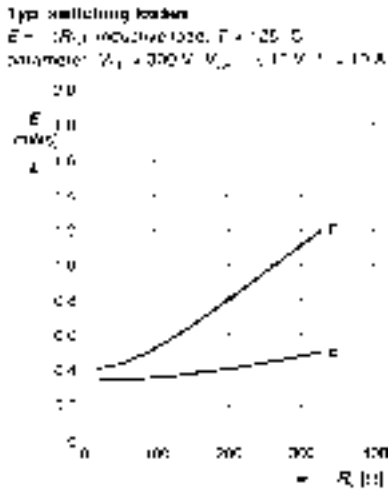
POWERSEM GmbH, Walpersdorfer Str. 53
D - 91126 Schwabach
Phone: 09122 - 9764 - 0 FAX: 09122 - 9764 - 20

IGBT

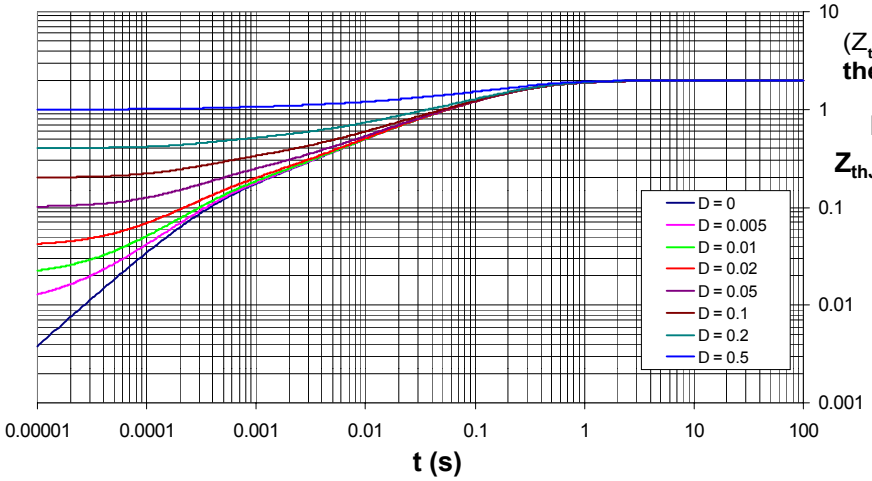








Transient thermal resistance junction to heatsink



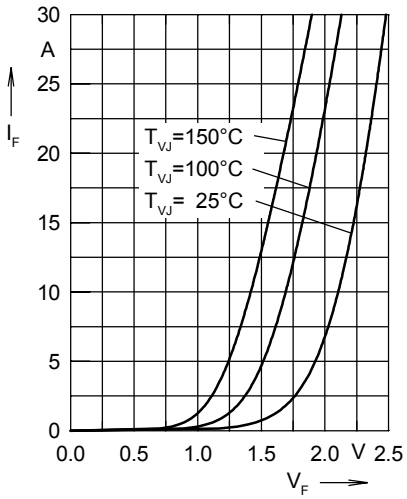
(Z_{thJH} **is measured using 50 µm thermal grease)**

IGBT

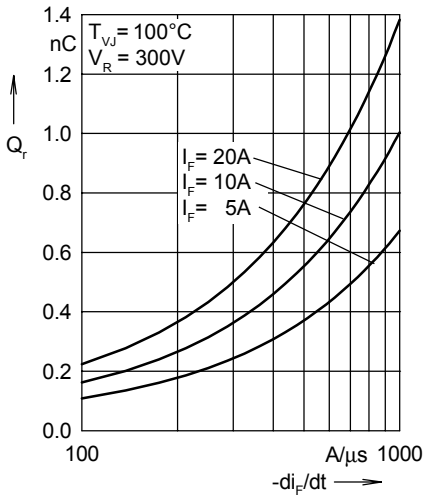
Z_{thJH} [K/W]

POWERSEM GmbH, Walpersdorfer Str. 53
D - 91126 Schwabach
Phone: 09122 - 9764 - 0 FAX: 09122 - 9764 - 20

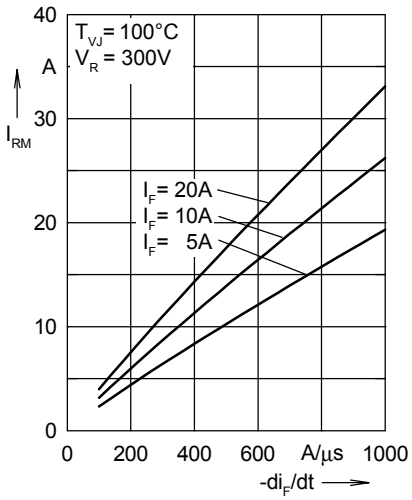
Diode



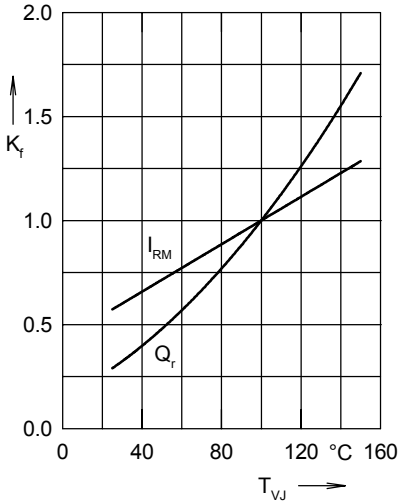
Forward current I_F versus V_F



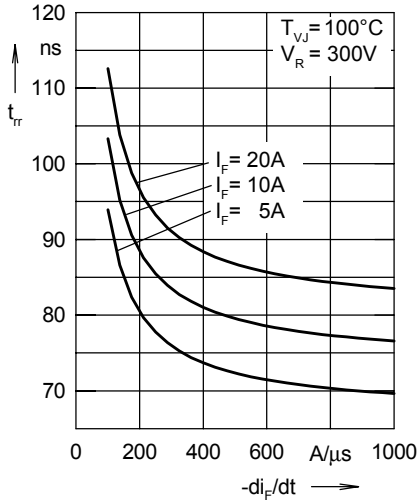
Reverse recovery charge Q_r versus -di_F/dt



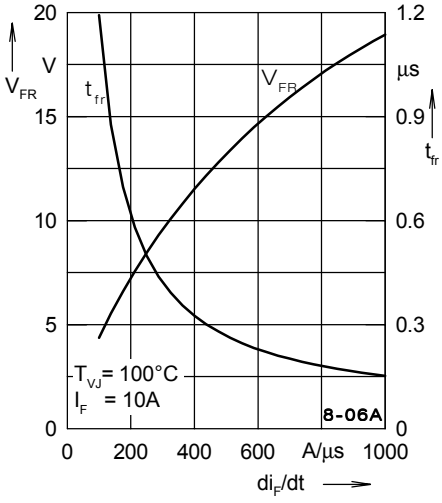
Peak reverse current I_{RM} versus -di_F/dt



Dynamic parameters Q_r, I_{RM} versus T_{VJ}

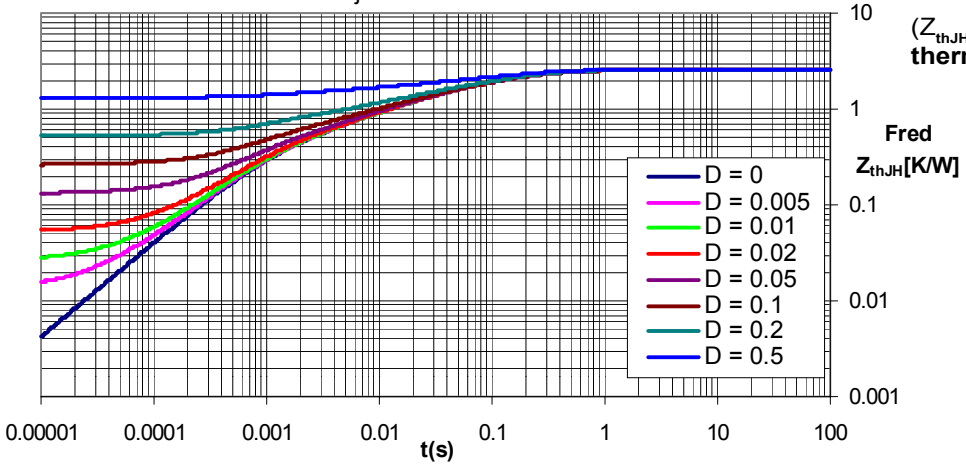


Recovery time t_{rr} versus -di_F/dt



Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

Transient thermal resistance junction to heatsink



(Z_{thJH} is measured using 50 µm thermal grease)

POWERSEM GmbH, Walpersdorfer Str. 53
D - 91126 Schwabach
Phone: 09122 - 9764 - 0 FAX: 09122 - 9764 - 20

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for IGBT Modules ***category:***

Click to view products by Powersem ***manufacturer:***

Other Similar products are found below :

F3L100R07W2E3_B11 F3L15R12W2H3_B27 F3L400R07ME4_B22 F3L400R12PT4_B26 F4-100R12KS4 F4-50R07W2H3_B51 F4-75R12KS4_B11 FB15R06W1E3 FB20R06W1E3_B11 FD1000R33HE3-K FD200R12KE3 FD300R06KE3 FD300R12KE3 FD300R12KS4_B5 FD400R12KE3 FD400R33KF2C-K FD401R17KF6C_B2 FD-DF80R12W1H3_B52 FF100R12KS4 FF1200R17KE3_B2 FF150R12KE3G FF200R06KE3 FF200R06YE3 FF200R12KT3 FF200R12KT3_E FF200R12KT4 FF200R17KE3 FF300R06KE3_B2 FF300R12KE4_E FF300R12KS4HOSA1 FF300R12ME4_B11 FF300R12MS4 FF300R17ME4 FF450R12ME4P FF450R17IE4 FF600R12IE4V FF600R12IP4V FF800R17KE3 FF800R17KP4_B2 FF900R12IE4V MIXA30W1200TED FP06R12W1T4_B3 FP100R07N3E4 FP100R07N3E4_B11 FP10R06W1E3_B11 FP10R12W1T4_B11 FP10R12YT3 FP10R12YT3_B4 FP150R07N3E4 FP15R12KT3